What is claimed is:

1. An inorganic material film comprising:
a chromium-containing material, and
a light-shielding layer having electrical conductivity,
wherein:
the light-shielding layer comprises 0.1 atomic percent to 11.5 atomic percent of tin and 15 atomic percent or less of oxygen; and
the inorganic material film has an arithmetic average roughness (Ra) of 1.0 nm or less.

2. The inorganic material film according to claim 1, further comprising an anti-reflection layer film formed by sputtering and comprising a chromium-containing material.

3. The inorganic material film according to claim 2, wherein the anti-reflection layer comprises tin.

4. The inorganic material film according to claim 2, having a stacked structure comprising the light-shielding layer and the anti-reflection layer.

5. The inorganic material film according to claim 1, having a resistance value of 5000 Ω/cm^2 or smaller.

6. The inorganic material film according to claim 1, wherein an oxygen concentration in the light-shielding layer is 3 atomic percent or higher.

7. The inorganic material film according to claim 1, wherein the chromium-containing material is selected from the group consisting of chromium metal, chromium oxide, chromium nitride, chromium carbide, chromium oxide nitride, chromium oxide carbide, and chromium oxide nitride carbide.

8. A photomask blank comprising the inorganic material film according to claim 1 as a light-shielding film, a hard mask film, or an etching stopper film.

9. A method for manufacturing a photomask, comprising patterning the inorganic material film by chlorine-containing dry etching using the photomask blank according to claim 8.